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3

1 COT

2a 2e

3 COT

(12) (13) (15) (14)

(15) (16a, 16b) (12) (16a) (16b) (T)

(12) (16a)

(16a, 16b) 1 (11) (T) (17)

(17) (18)가 (18) (17)

(16b) (19) 가

(18) (19) (16b) (20)

1 (11) 1 (11) 가 2 (21) (21) (22)가 (T) 가

(22) (20) 가 가

(22) (T) (20) 가 가

(22) 2 (21) (23)

(20) (23) (30) (30)

가 (20) (23) 가 (20, 23) (23)

(18) 1 () (11) 1 (11) 2 () (21) (18) (20)

(18) 1 (11) 1 (11) 2 (21) (18) (20) 2 (21) (2)

2a 2e

2a 1 (11) 1

(12) (12) 1 (

(12) 1 (11) (13)

2

(14) (15) .

2b , 1 (11) (16a) , 3 (16b) .

, (16a) (16b) (16a) 2
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(16a) (16b) (15) .

, (16a) (16b) ,

, (16a,16b) (12) (T) .

, 2c , (16a, 16b)
(17) (17) ,
(T) .

, 2d , (17)
(18) (16b) (18) (17) ,
(16b) (19) .

, (18) , , 가 ,

, 2e , (18) (18)
(19) (16b) (20)

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가

가

3 COT

3 (51) (52) 가 (52) (51)

(51) (53) (54) (55)

(52) (53) (54) (55)

(54) (55)

(55) (56a) (56b) (52)

(56a, 56b) (52) (T)

(56a, 56b) (57)가 (57)

(56b) (56b) (59) 가

(58)

(57) (60) (59) (60) (58)

(56b)

가 가

가

4a 4g

4a 4g

4a , (51) (52) (52) ,
1 () .
, Al, Al-Pd, Al-Si, Al-Si-Ti, Al-Si-Cu, Al
200~4000 .
4b , (52) (51) (53),
(54a), (55a)
(55a) (56) CVD , (56)
() (57)
, (-) ,
, (57) .
4c , (57) (56),
(55a), (54a) .
4d , (57) O₂ (ashing) (57)
, (57) 가
, (57)
(56) (55) (54) (55a) (56a) (56b)
(56a) 2
() (T) , (56a) (56b)
(52) (T) .
4e , (57) (56a) (56b)
(51) (58a) , (56a) (56b)
1 가
(T)가 (51) .
9) (56b) 4f , (5
(58) .
, (58) , 가 2 3
. .
4g , (59) (51) - - (indium-tin-oxide)
) - - (indium-zinc-oxide)
(56b) (60) .
, (60) (58) (
) .
, 가 , 가
가 .

가 .

가 , 가 , 가 .

(57)

1.

2.

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3.

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4.

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가

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7.

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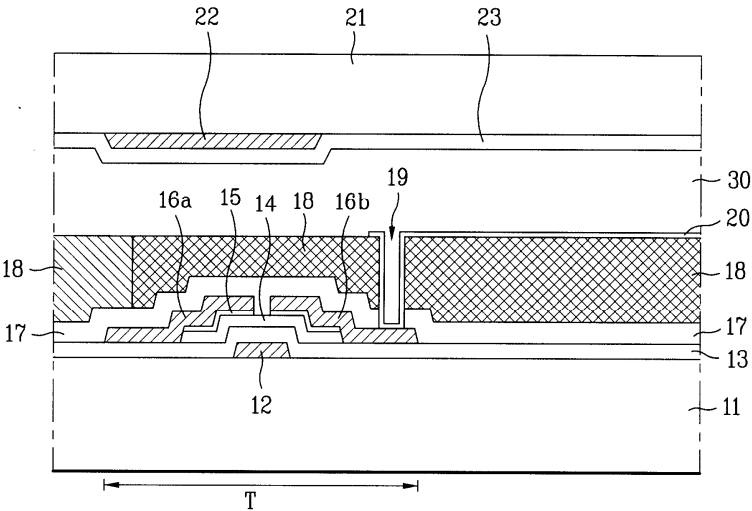
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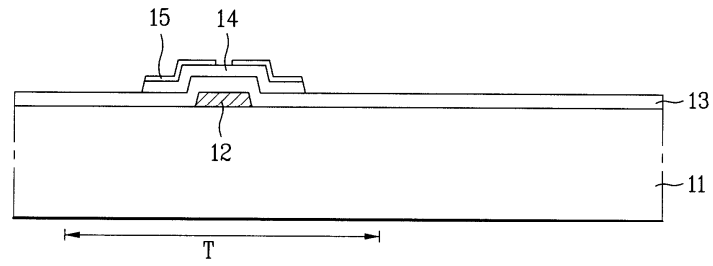
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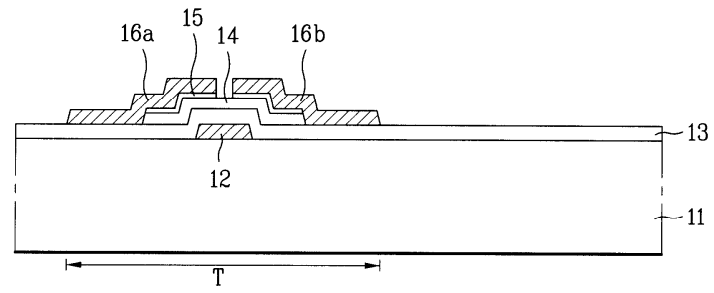
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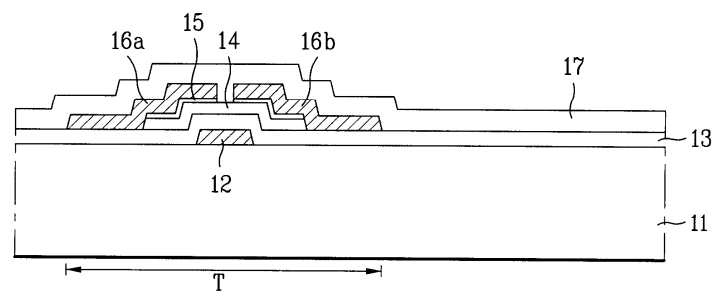
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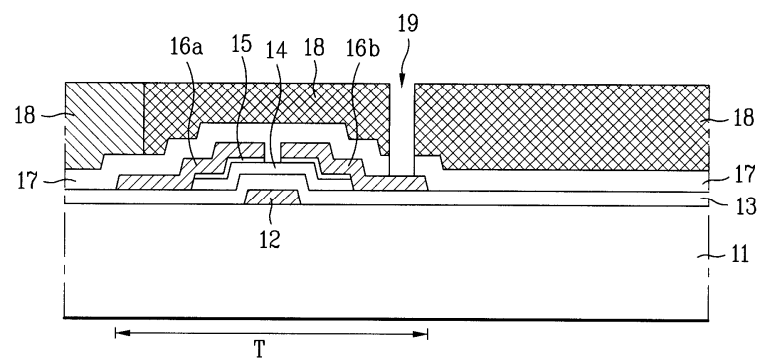
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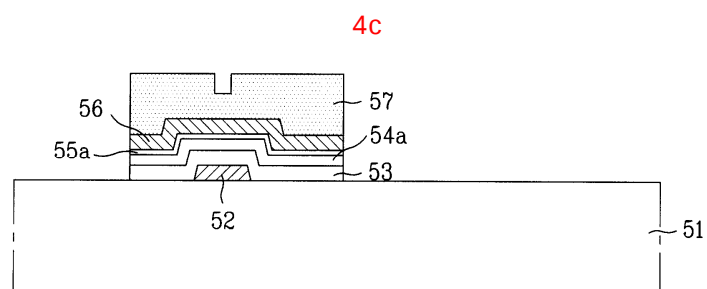
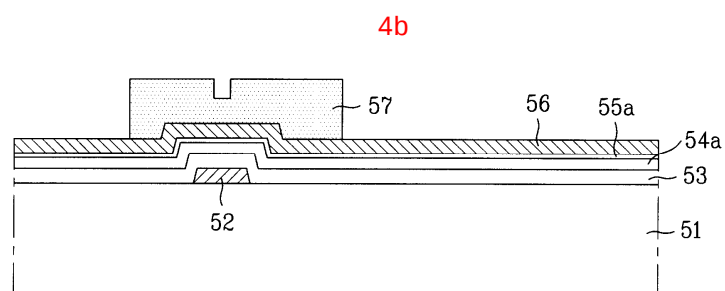
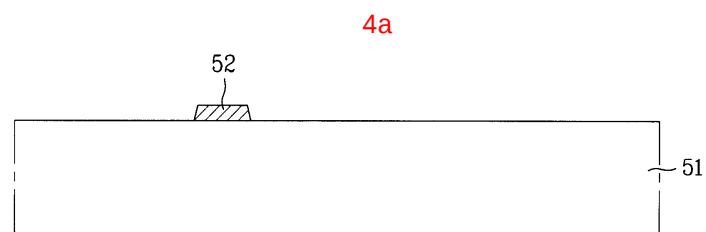
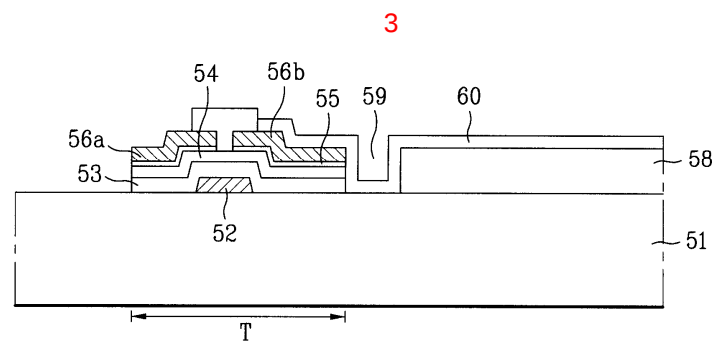
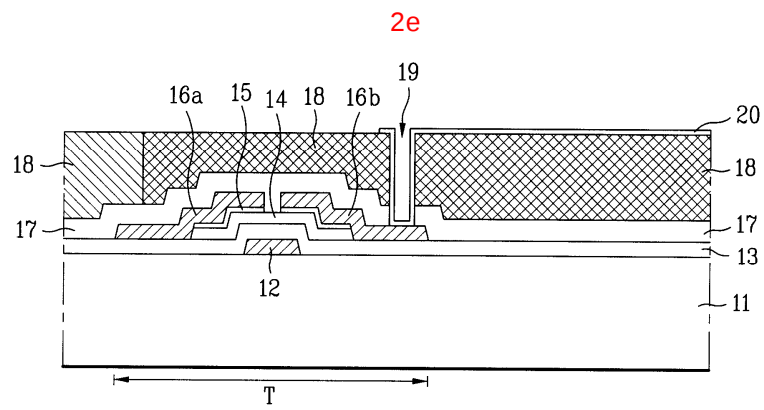


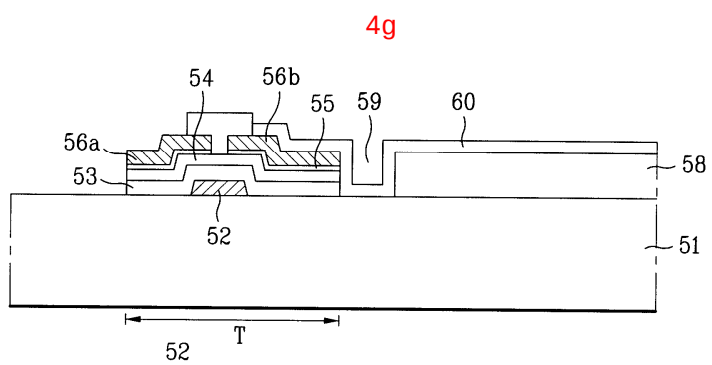
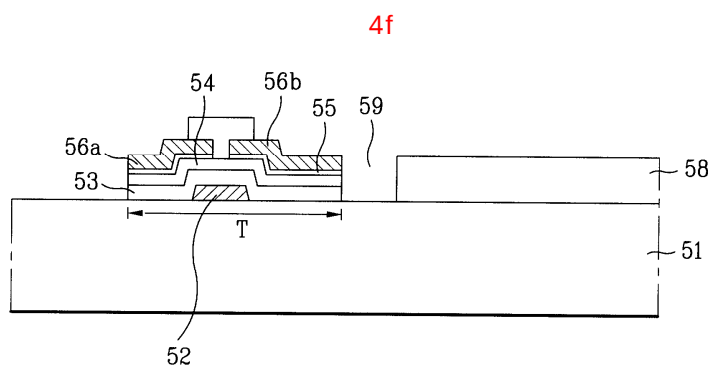
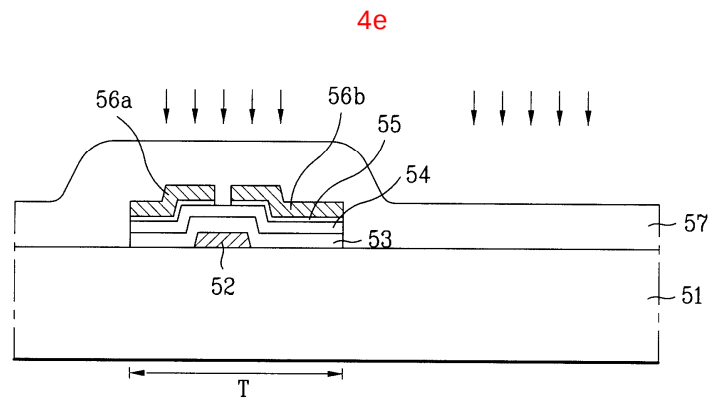
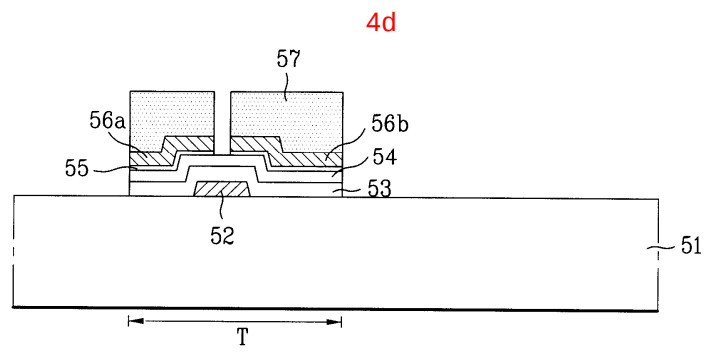
2c



2d







专利名称(译)	用于液晶显示装置的阵列基板及其制造方法		
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[标]申请(专利权)人(译)	乐金显示有限公司		
申请(专利权)人(译)	LG显示器有限公司		
当前申请(专利权)人(译)	LG显示器有限公司		
[标]发明人	KIM JEONGHYUN 김정현 KIM SAMYEOL 김삼열		
发明人	김정현 김삼열		
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代理人(译)	金勇 新昌		
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摘要(译)

液晶显示装置用阵列基板及其制造方法技术领域本发明涉及一种液晶显示装置用阵列基板及其制造方法，在提高液晶显示装置的开口率的同时简化制造工艺，阵列基板包括栅极布线和与绝缘基板交叉的数据布线，一种薄膜晶体管，包括在栅极线和数据线的交叉点处的栅电极和源电极以及漏电极，以及具有接触孔的薄膜晶体管，使得漏电极的表面在预定部分处暴露，并且像素电极通过接触孔连接到漏电极并形成在滤色器上。3 指数方面 滤色片，热转印方法，掩模，孔径比

